

INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

SETI-0004

Application Number

Applicant(s)

Gaska et al.

Filing Date

Group Art Unit

*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Temperature Effect on the Quality of AlN Thin Films," M. P. Thompson et al., MRS Internet J. Nitride Semicond. Res. 4S1, G3.7 (1999).

"High Rate and Selective Etching of GaN, AlaN, and AlN Using an Inductively Coupled Plasma," S. A. Smith et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3631-3633.

"Reactive Sputter Deposition of Highly Oriented AlN Films at Room Temperature," G.F. Iriarte et al., J. Mater. Res., Vol. 17, No. 6, June 2002, pp. 1469-1475.

"PVT Growth of Bulk AlN Crystals With Low Oxygen Contamination," M. Bickermann et al., Phys. Stat. Sol. (a), Vol. 195, No. 1, 3-10 (2003), pp. 1 - 4.

"Introduction to Solid-State Lighting," Zukauskas et al., pp. 61-69. (2002).

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DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.